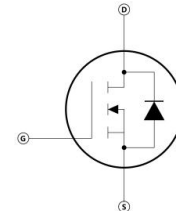
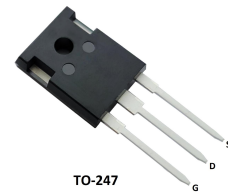


Features

- 100% avalanche tested
- Fast Intrinsic Diode
- Gate charge minimized
- Very low intrinsic capacitances
- High speed switching



Applications

- High Voltage Power Supplies
- PV Inverter
- Switching applications

Electrical ratings

Absolute maximum ratings			
Parameter	Symbol	Value	Unit
Drain-source voltage ($V_{GS} = 0$)	V_{DS}	2500	V
Transient Gate- source voltage	V_{GSM}	± 30	
Continuous Gate- source voltage(DC)	V_{GSS}	± 20	
Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	I_D	4	A
Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$		2.5	
Drain current (pulsed)	I_{DM}	12	
Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	P_D	520	W
Avalanche Current	I_{AR}	2.6	A
Single pulse avalanche energy (starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$, $L = 20\text{ mH}$)	E_{AS}	67.6	mJ
Operating junction temperature	T_J	-55 ~ 150	$^{\circ}\text{C}$
Storage temperature	T_{stg}		
Maximum lead temperature for soldering purpose	T_L	300	$^{\circ}\text{C}$
Mounting Torque	M_d	1.13	N • m
Weight	G	6	g

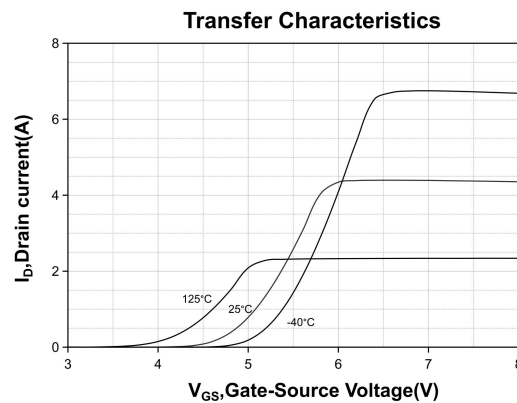
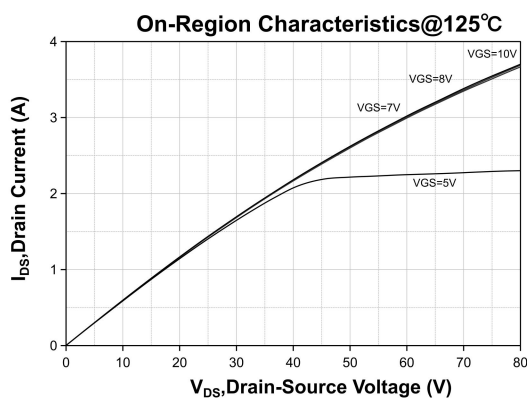
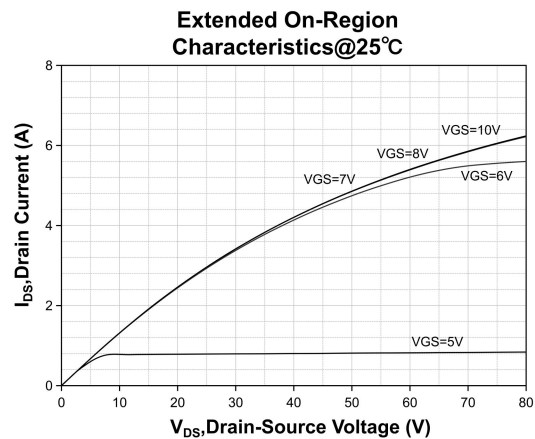
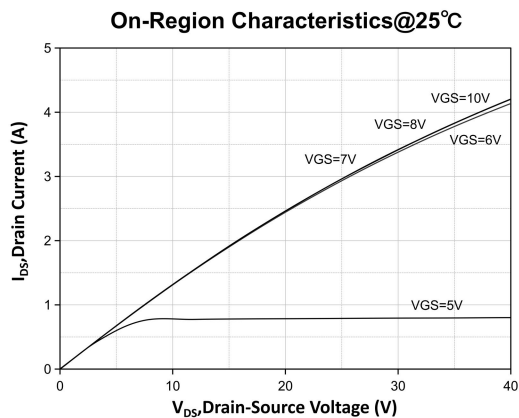
Electrical Characteristics ($T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

On /off states						
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	2500			V
Zero gate voltage drain current ($V_{GS} = 0$)	I_{DSS}	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125^{\circ}\text{C}$			100 1000	μA
Gate-body leakage current ($V_{DS} = 0$)	I_{GSS}	$V_{GS} = \pm 20\ \text{V}$			± 200	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	3.5	-	5.5	V
Static drain-source on resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 2\text{A}$	-	19	25	Ω

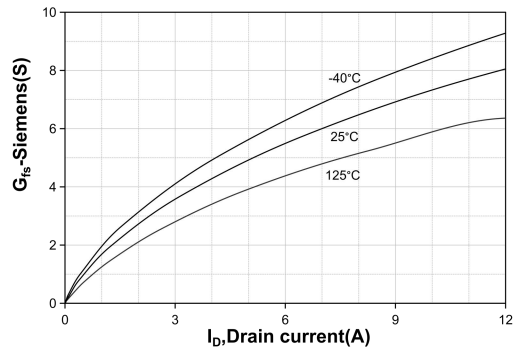
Dynamic						
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Forward transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 2\text{ A}$	1.2	2.7		S
Input capacitance	C_{iss}	$V_{DS}=25\text{ V}, f=1\text{ MHz}, V_{GS}=0$		1540		pF
Output capacitance	C_{oss}			110		
Reverse transfer capacitance	C_{rss}			48		
Total gate charge	Q_g	$V_{DD}=1250\text{ V}, I_D=2\text{ A}$ $V_{GS}=10\text{ V}$		74		nC
Gate-source charge	Q_{gs}			7		
Gate-drain charge	Q_{gd}			43		
Switching times						
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Turn-on delay time	$t_{d(on)}$	Resistive load $V_{DD} = 1250\text{ V}, I_D = 2\text{ A},$ $V_{GS} = 10\text{ V},$ $R_G = 5\Omega(\text{External})$		19		ns
Rise time	t_r			23		
Turn-off-delay time	$t_{d(off)}$			52		
Fall time	t_f			53		
Source drain diode						
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Source-drain current	I_{SD}				4	A
Source-drain current (pulsed)	I_{SDM}				12	

Forward on voltage	V _{SD}	I _{SD} = 4A, V _{GS} = 0			1.5	V
Reverse recovery time	t _{rr}	I _{SD} =2A, -di/dt=100A/μs V _{DD} = 100 V		600		ns
Reverse recovery charge	Q _{rr}			540		nC
Reverse recovery current	I _{RRM}			1.2		A
Reverse recovery time	t _{rr}	I _{SD} =2A, di/dt=100A/μs V _{DD} = 100 V T _J =150°C		800		ns
Reverse recovery charge	Q _{rr}			420		nC
Reverse recovery current	I _{RRM}			1.5		A
Thermal data						
Parameter			Symbol	Value		Unit
Thermal resistance junction-case max			R _{thj-case}	0.24		°C/W
Thermal resistance junction-ambient max			R _{thj-amb}	50		

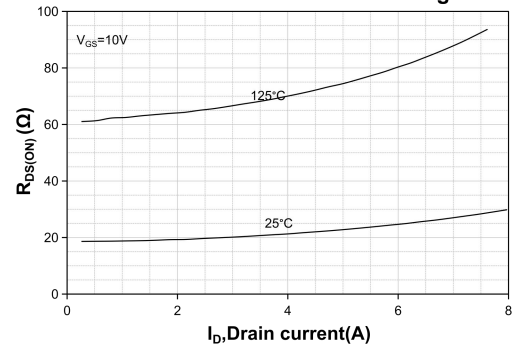
Electrical characteristics



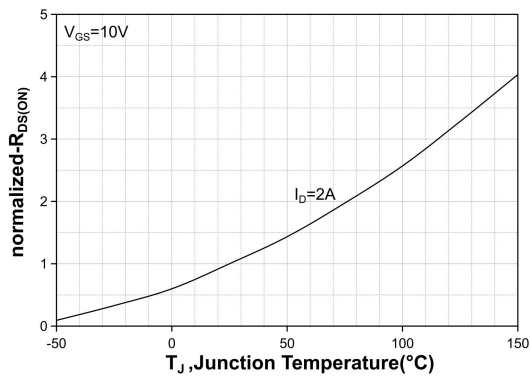
Transconductance



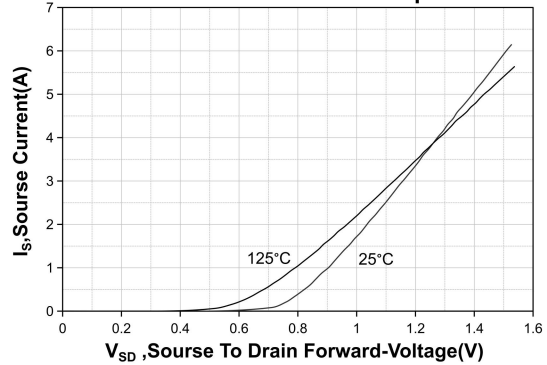
On-Resistance Variation vs Drain Current and Gate Voltage



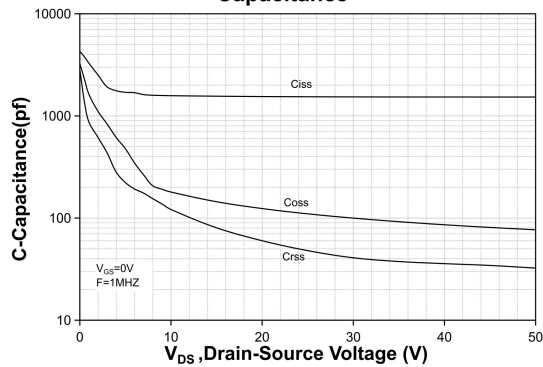
On-Resistance Variation vs Temperature



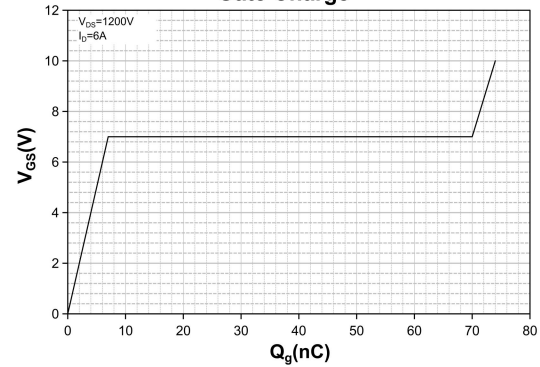
Body Diode Forward Voltage Variation with Source Current and Temperature



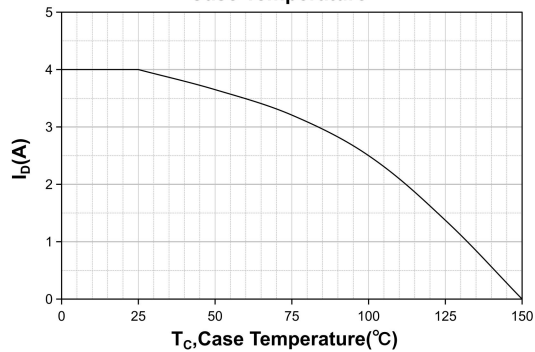
Capacitance



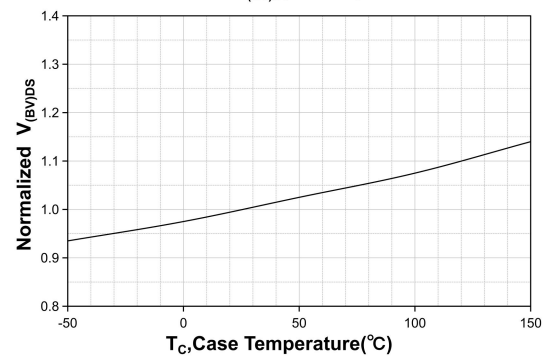
Gate Charge

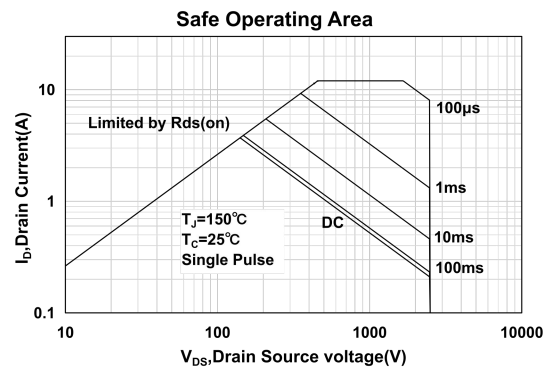
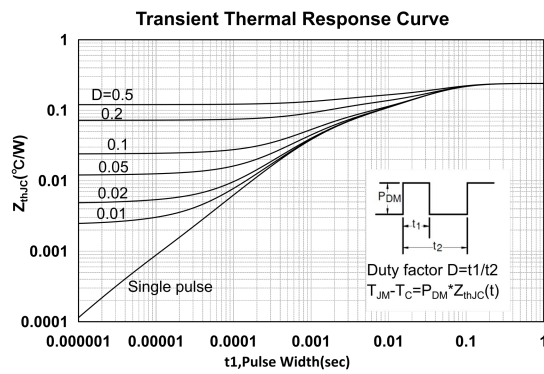


Maximum Drain Current vs Case Temperature



Normalized $V_{(BV)DS}$ vs temperature





Package outline dimension

